

SS34-320

Schottky Barrier Diode



Features

- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- Metal silicon junction, majority carrier conduction
- Approx. Weight : 15mg



Pb Free

ROHS Compliant

Green Product

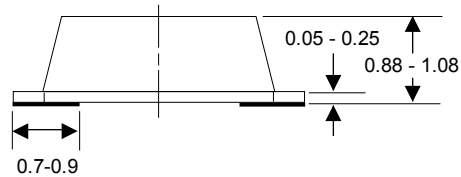
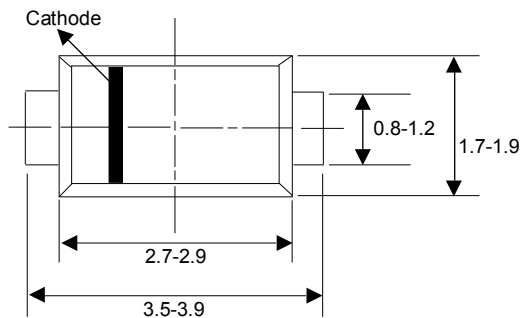
Making :

SS34	K34
SS36	K36
SS310	K310
SS320	K320



PACKAGE DIMENSIONS in millimeters (mm):

SOD-123F



Packing : 3000pcs/reel

Maximum Ratings And Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbols	SS34	SS36	SS310	SS320	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	40	60	100	200	V
Maximum RMS voltage	V _{RMS}	28	42	70	140	V
Maximum DC Blocking Voltage	V _{DC}	40	60	100	200	V
Maximum Average Forward Rectified Current	I _{F(AV)}	3.0				A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	80				A
Max Instantaneous Forward Voltage at 3A	V _F	0.55	0.70	0.85	0.95	V
Maximum DC Reverse Current T _a = 25°C At Rated DC Reverse Voltage T _a =100°C	I _R	0.5 10	0.3 5			mA
Typical Junction Capacitance ⁽¹⁾	C _j	250	160			pF
Typical Thermal Resistance ⁽²⁾	R _{θJA}	80				°C/W
Operating Junction Temperature Range	T _j	-55 ~ +125				°C
Storage Temperature Range	T _{stg}	-55 ~ +150				°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

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Typical Characteristics

Fig.1 Forward Current Derating Curve

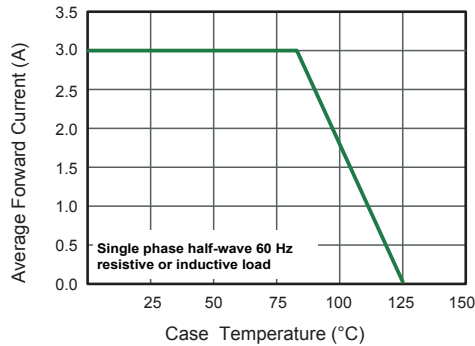


Fig.2 Typical Reverse Characteristics

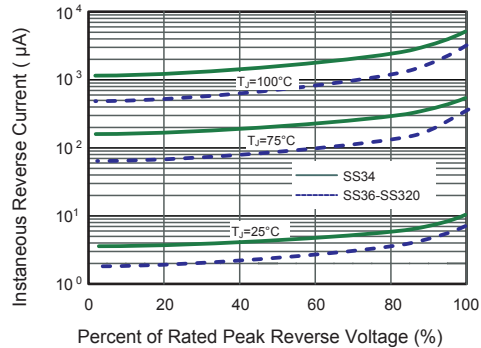


Fig.3 Typical Forward Characteristic

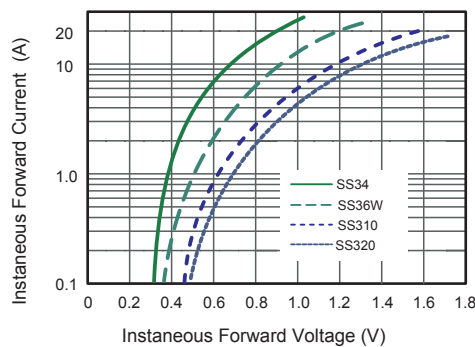


Fig.4 Typical Junction Capacitance

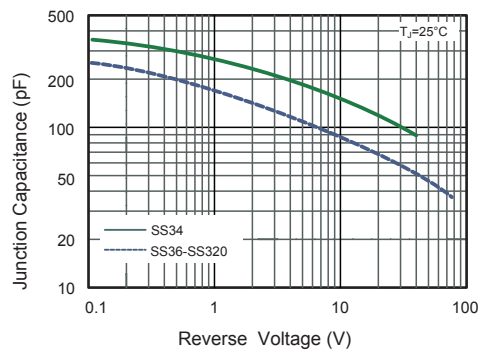


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

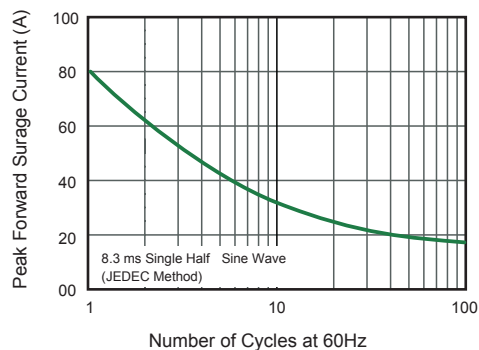


Fig.6 Typical Transient Thermal Impedance

